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Effects of ferroelectric and ferromagnetic buffer layers in CMR epitaxial films

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Perovskite ferromagnetic and ferroelectric buffer layers on the LaAlO_3 (001) substrate for colossal-magnetoresistance (CMR) epitaxial film play an important role for the magnetic and the transport properties. $\text{La}_{0.8}\text{Ca}_{0.2}\text{MnO}_3$ and BaTiO_3 were prepared as the buffer layers by the 'soft'-target magnetron sputtering. By using X-ray diffraction and high-resolution electron microscopy, we observed that the out-of-plane uniaxial tensile strains occur in CMR/CMR films, but the strain for a $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$ film without the $\text{La}_{0.8}\text{Ca}_{0.2}\text{MnO}_3$ buffer layer is larger than that with the buffer layer. It is shown that the metal-insulator and the ferromagnetic transitions turn out to be shifted to higher temperatures for $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$ on $\text{La}_{0.8}\text{Ca}_{0.2}\text{MnO}_3$ compared with the bare $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$.

However, the metal-insulator transition was not observed in a temperature range of 10 to 300 K in the CMR film on a BaTiO_3 buffer layer. The enhanced magnetoresistance and ferromagnetic ordering in the $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3/\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$ bilayer are elucidated with the lattice-strain relaxation in the $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$ layer. On the other hand, the discovered suppression of contribution from the Jahn-Teller distortion to the ferromagnetic ordering with increasing the lattice mismatch between substrate and film manifests a physical limit of the weak-strain approach in describing the magnetic properties of manganite films.